

This device is designed for use in low noise UHF/VHF amplifiers with collector currents in the 100 µA to 30 mA range in common emitter or common base mode of operation, and in low frequency drift, high ouput UHF oscillators. Sourced from Process 40.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	12	V
V _{CBO}	Collector-Base Voltage	20	V
V _{EBO}	Emitter-Base Voltage	2.5	V
Ic	Collector Current - Continuous	50	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES: 1) These ratings are based on a maximum junction temperature of 150 degrees C. 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах		Units	
		PN/MPS5179	*MMBT5179		
PD	Total Device Dissipation Derate above 25°C	350 2.8	225 1.8	mW mW/°C	
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient	357	556	°C/W	

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

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NPN RF Transistor

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHAI	RACTERISTICS				
V _{CEO(sus)}	Collector-Emitter Sustaining Voltage*	$I_{\rm C} = 3.0 \text{ mA}, I_{\rm B} = 0$	12		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{C} = 1.0 \ \mu A, \ I_{E} = 0$	20		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{E} = 10 \ \mu A, I_{C} = 0$	2.5		V
сво	Collector Cutoff Current	$V_{CB} = 15 \text{ V}, \text{ I}_{E} = 0$ $V_{CB} = 15 \text{ V}, \text{ T}_{A} = 150^{\circ}\text{C}$		0.02 1.0	μΑ μΑ
ON CHAR	ACTERISTICS DC Current Gain	I _C = 3.0 mA, V _{CE} = 1.0 V	25	250	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 1.0 \text{ mA}$		0.4	V
CE(Sal)				1.0	V

SMALL SIGNAL CHARACTERISTICS

f _T	Current Gain - Bandwidth Product	$I_{C} = 5.0 \text{ mA}, V_{CE} = 6.0 \text{ V},$ f = 100 MHz	900	2000	MHz
C _{cb}	Collector-Base Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0,$ f = 0.1 to 1.0 MHz		1.0	pF
h _{fe}	Small-Signal Current Gain	$I_{C} = 2.0 \text{ mA}, V_{CE} = 6.0 \text{ V},$ f = 1.0 kHz	25	300	
rb'C _c	Collector Base Time Constant	$I_{C} = 2.0 \text{ mA}, V_{CB} = 6.0 \text{ V},$ f = 31.9 MHz	3.0	14	ps
NF	Noise Figure	$I_{C} = 1.5 \text{ mA}, V_{CE} = 6.0 \text{ V}, R_{S} = 50\Omega, f = 200 \text{ MHz}$		5.0	dB

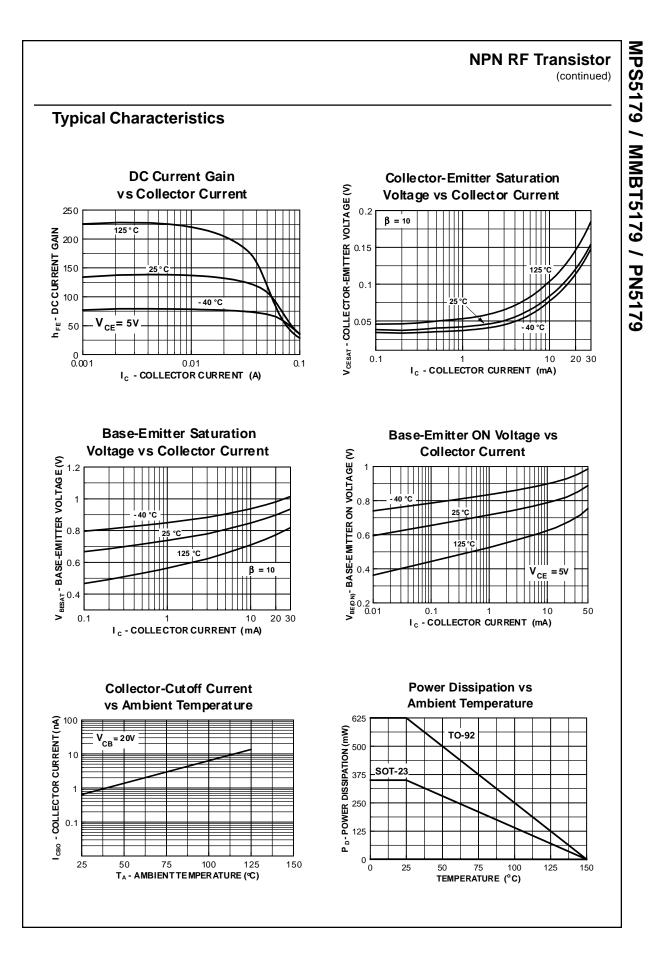
FUNCTIONAL TEST

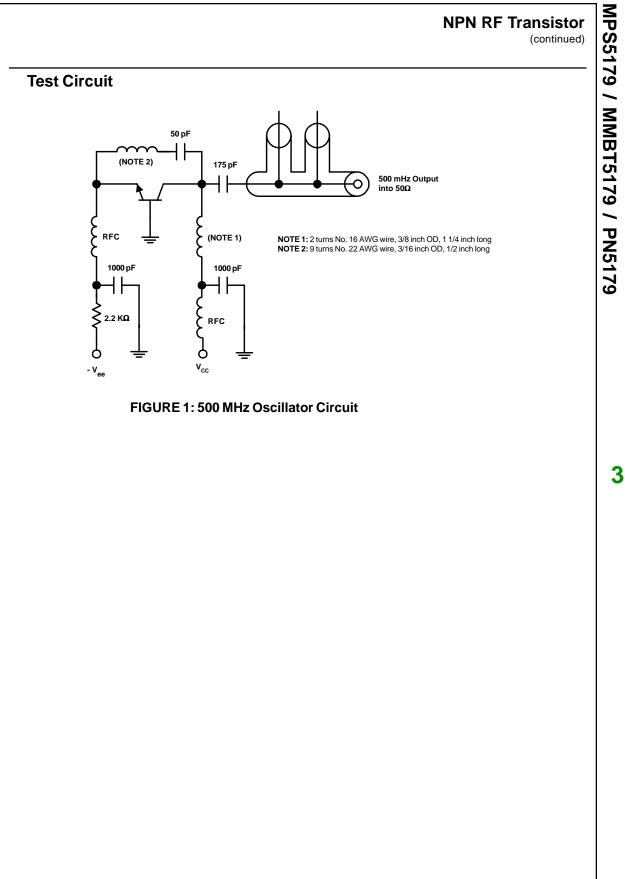
G _{pe}	Amplifier Power Gain	$V_{CE} = 6.0 \text{ V}, I_C = 5.0 \text{ mA},$ f = 200 MHz	15	dB
Po	Power Output	V_{CB} = 10 V, I_E = 12 mA, f ≥ 500 MHz	20	mW

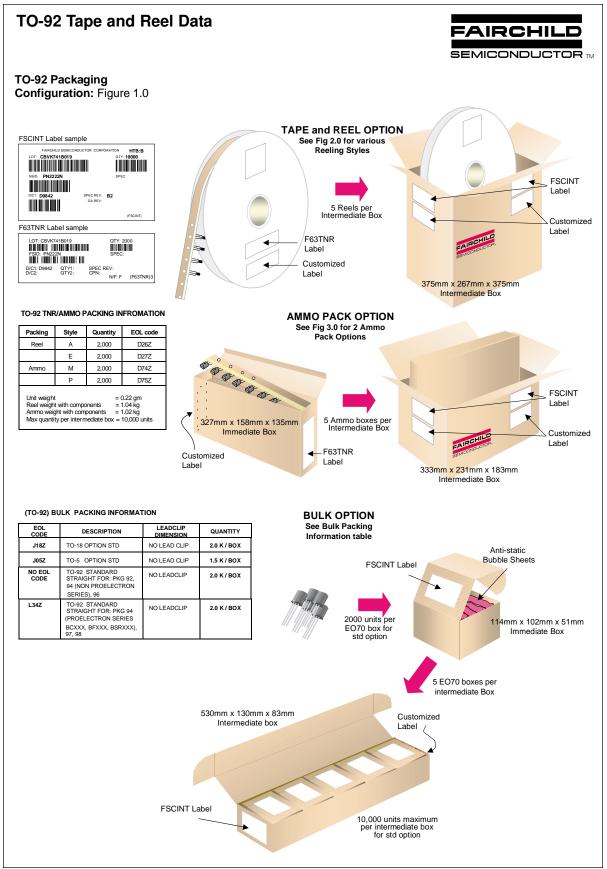
*Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

Spice Model

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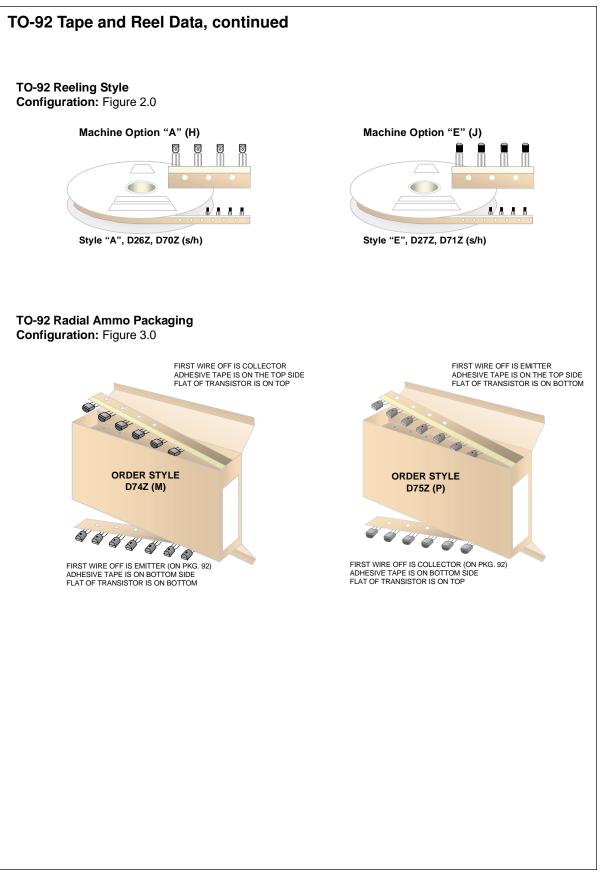


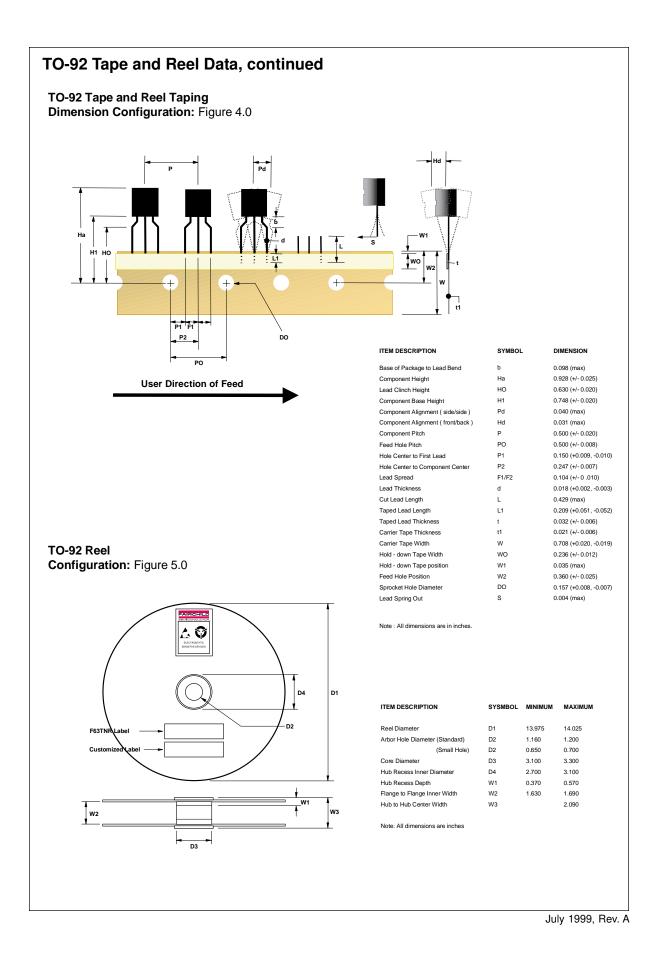


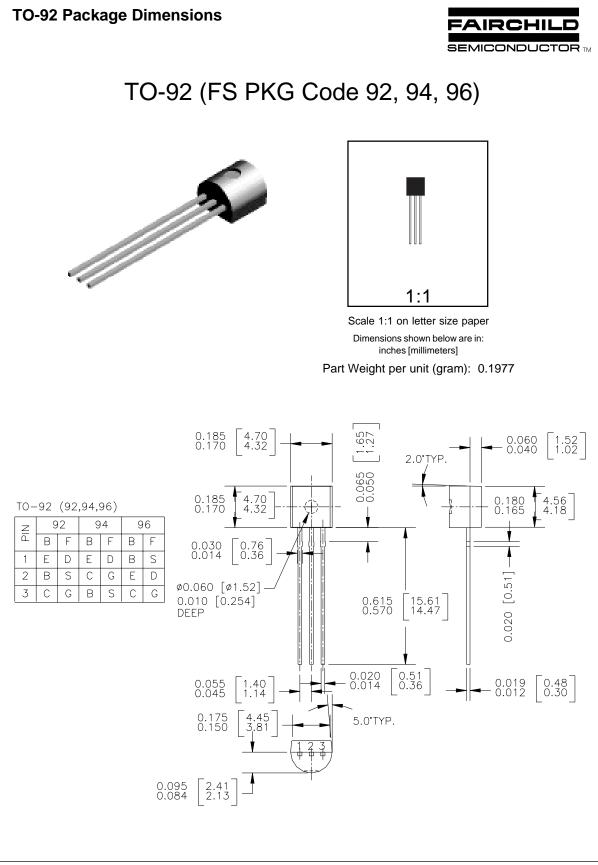


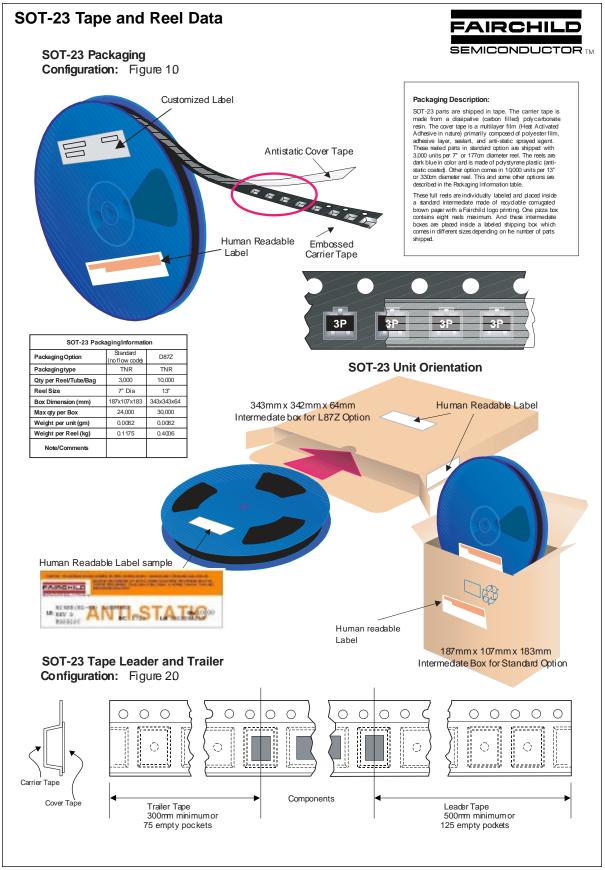
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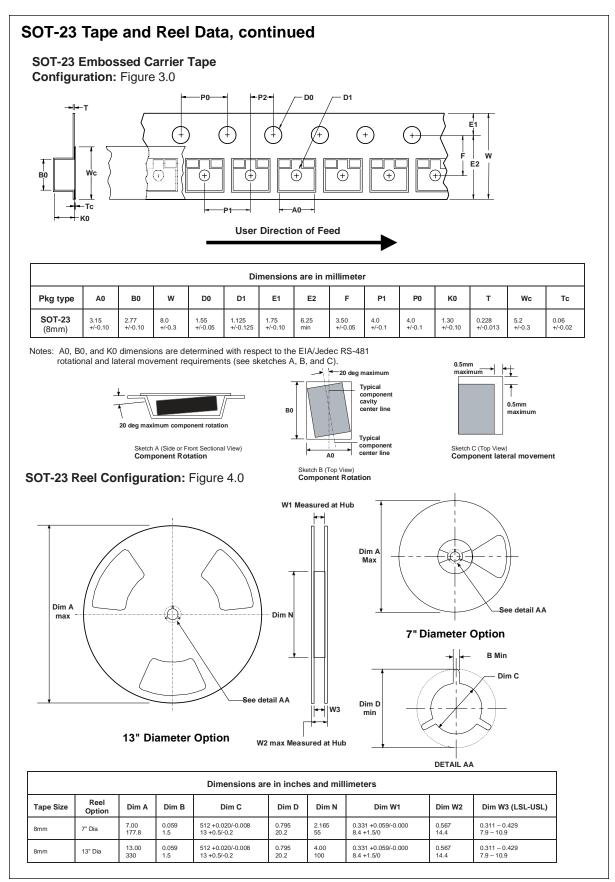




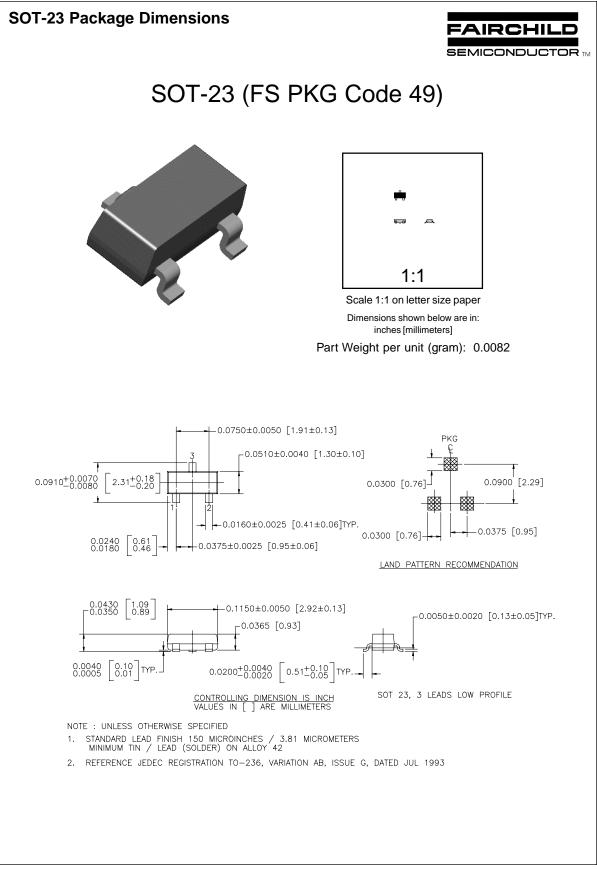


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